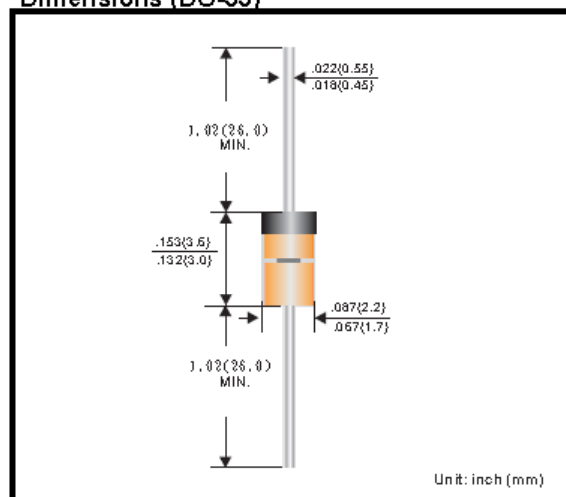


Absolute Maximum Ratings (Ta=25°C)			
Items	Symbol	Ratings	Unit
Reverse Voltage	V_R	50	V
Reverse Recovery Time	T_{rr}	4	ns
Power Dissipation 3.33mW/ °C (25°C)	P	500	mW
Forward Current	I_F	200	mA
Junction Temp.	T_j	-65 to 175	°C
Storage Temp.	T_{stg}	-65 to 175	°C

Mechanical Data	
Items	Materials
Package	DO-35
Case	Hermetically sealed galss
Lead/ Finish	Double stud/ Solder Plating
Chip	Glass Passivated

Dimensions (DO-35)



Electrical Characteristics (Ta=25°C)			
Parameter	Symbol	Limit	Unit
Minimum Breakdown Voltage $I_R = 5.0\mu A$	V_R	50	V
Peak Forward Surge Current PW= 1sec.	I_F surge	1	A
Maximum Forward Voltage $I_F = 200mA$	V_F	1	V
Maximum Reverse Current $V_R = 50V$ $V_R = 20V, T_j = 150^\circ C$	I_R	0.1 100	μA
Maximum Junction Capacitance $V_R = 0, f = 1 MHz$	C_j	2.5	pF
Maximum Reverse Recovery Time $I_F = 10mA, V_R = 6V, I_{RR} = 1mA, R_L = 100\Omega$	T_{rr}	4	ns

●Electrical characteristic curves ($T_a = 25^\circ\text{C}$ unless specified otherwise)

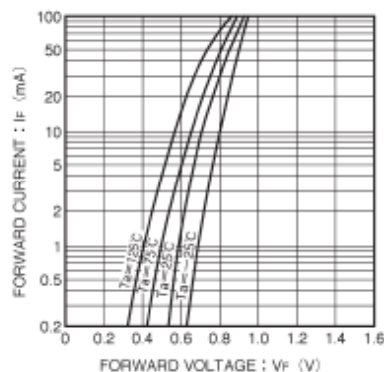


Fig. 1 Forward characteristics

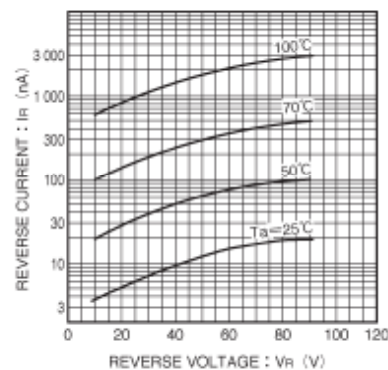


Fig. 2 Reverse characteristics

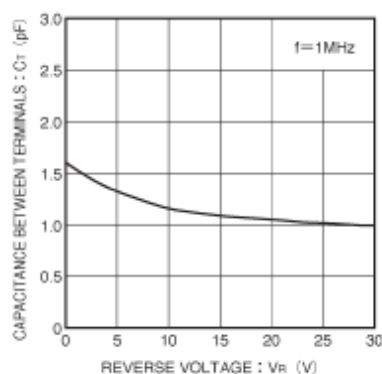


Fig. 3 Capacitance between terminals characteristics

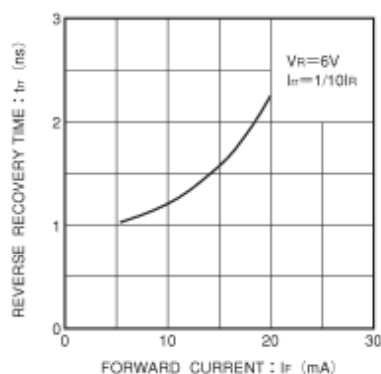


Fig. 4 Reverse recovery time characteristics

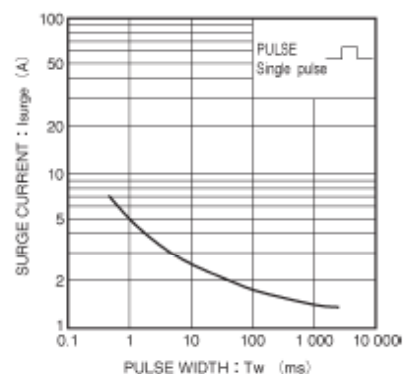


Fig. 5 Surge current characteristics

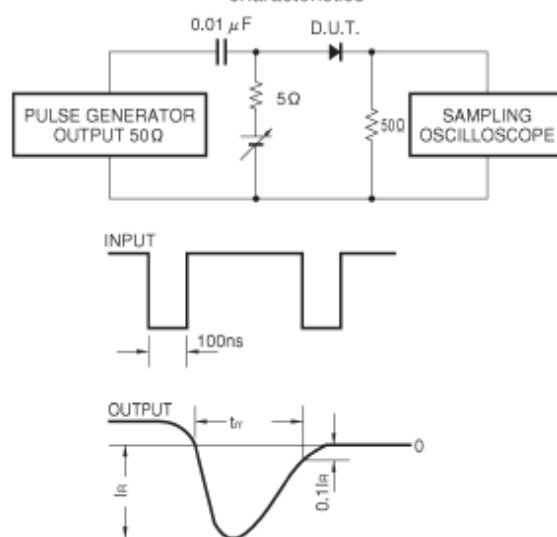


Fig. 6 Reverse recovery time (t_{rr}) measurement circuit